Supporting Information

Low Band-gap Conjugated Polymer based on Diketopyrrolopyrrole

Units and its Application in Organic Photovoltaic

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| D/A | V_{oc} (V) | J_{sc} (mA/cm ²) | FF | PCE (%) |
|-------|--------------|--------------------------------|-------|---------|
| 1:1 | 0.734 | 15.85 | 0.557 | 6.48 |
| 1:1.5 | 0.712 | 16.66 | 0.606 | 7.18 |
| 1:2 | 0.705 | 16.02 | 0.646 | 7.30 |
| 1:3 | 0.711 | 14.35 | 0.672 | 6.85 |

Table S1. The optimization of D/A weight ratio of the P266: PC₇₁BM-based PSCs^a

a) 3% vol. DPE was used as additive here because that the primary PCE acquired fromCB is too low. The results were acquired from the conventional method.

| DPE (%) | Voc (V) | J_{sc} (mA/cm ²) | FF | PCE (%) |
|---------|---------|--------------------------------|-------|---------|
| 1 | 0.731 | 6.87 | 0.584 | 2.87 |
| 3 | 0.711 | 16.60 | 0.639 | 7.54 |
| 5 | 0.693 | 17.14 | 0.598 | 7.10 |

Table S2. The optimization of additive feed ratio of the P266: PC71BM-based PSCs^a

a) The D/A weight ratio adopted here is 1:2. The results were acquired from the conventional method.

Table S3. Photovoltaic Characteristics of P266/PC₇₁BM–based PSC Devices with different film thickness.

| Film Thickness(nm) | V _{oc} (V) | J _{sc} (mA/cm ²) | FF | PCE (%) |
|-----------------------|---------------------|---------------------------------------|-------|---------|
| 340 | 0.69 | 21.08 | 0.519 | 7.60 |
| 305 | 0.69 | 21.32 | 0.562 | 8.28 |
| 270 | 0.69 | 20.25 | 0.599 | 8.42 |
| 250 | 0.69 | 19.65 | 0.612 | 8.35 |
| 230 | 0.69 | 19.24 | 0.630 | 8.41 |
| 210 | 0.70 | 18.10 | 0.657 | 8.32 |

| 180 | 0.70 | 17.58 | 0.669 | 8.20 |
|-----|------|-------|-------|------|
| 160 | 0.71 | 17.63 | 0.699 | 8.72 |
| 130 | 0.71 | 17.54 | 0.701 | 8.76 |
| 100 | 0.72 | 17.30 | 0.716 | 8.92 |



Figure S1. The *J-V* curves of the P266:PC₇₁BM-based devices with various film thickness (nm)



Figure S2. The EQE curves of the P266:PC₇₁BM-based devices with various film thickness (nm)



Figu

re S3. *J-V* Characteristics of the hole-only devices used for SCLC fitting (both films thickness are 180nm)



Figure S4. *J-V* Characteristics of the hole-only devices of the samples prepared from sloution-mixing method (S-180nm and S-145 nm) and conventional method (C-180nm and C-130 nm).

| Table S4. Hole mobilities calculated from devices with different film thic | kness |
|--|-------|
|--|-------|

| Thickness | 180nm | 145nm | 130nm |
|---------------|-----------------------|----------------------|-----------------------|
| Solution- | 1.52×10 ⁻³ | 1.28×10-3 | |
| mixing Method | $cm^{2/}$ (V·s) | $cm^{2/}(V \cdot s)$ | |
| Conventional | 2.96×10 ⁻⁴ | | 3.47×10 ⁻⁴ |
| Method | $cm^{2}/(V \cdot s)$ | | $cm^{2}/(V \cdot s)$ |

Figure S5. The absorption spectra of the blend film prepared by two methods.